

	No.2553A	2SB1234/2SD1851
		PNP/NPN Epitaxial Planar Silicon Transistors
Driver Applications		

Features

- AF amp, solenoid drivers, LED drivers
- Darlington connection
- High DC current gain
- Very small-sized package permitting sets to be made smaller and slimer

(): 2SB1234

Absolute Maximum Ratings at $T_a=25^{\circ}\text{C}$

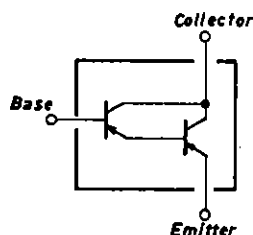
			unit
Collector to Base Voltage	V_{CBO}	(-)80	V
Collector to Emitter Voltage	V_{CEO}	(-)50	V
Emitter to Base Voltage	V_{EBO}	(-)10	V
Collector Current	I_C	(-)200	mA
Collector Current(Pulse)	I_{CP}	(-)400	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics at $T_a=25^{\circ}\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)60\text{V}, I_E=0$			(-)100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)8\text{V}, I_C=0$			(-)100	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=(-)2\text{V}, I_C=(-)10\text{mA}$	5000			
	$h_{FE(2)}$	$V_{CE}=(-)2\text{V}, I_C=(-)100\text{mA}$	4000			
			(3000)			
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100\text{mA}, I_B=(-)100\mu\text{A}$		(-)0.9	(-)1.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100\text{mA}, I_B=(-)100\mu\text{A}$		(-)1.5	(-)2.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$		(-)80		V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$		(-)50		V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$		(-)10		V

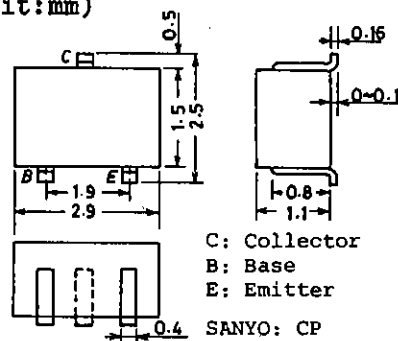
Marking 2SB1234:PL
2SD1851:XY

Electrical Connection

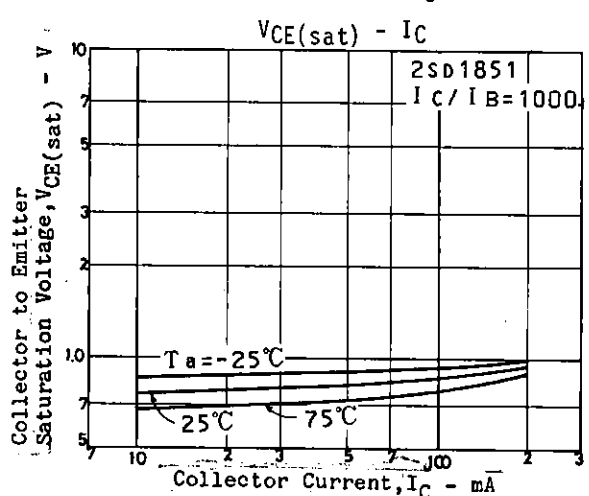
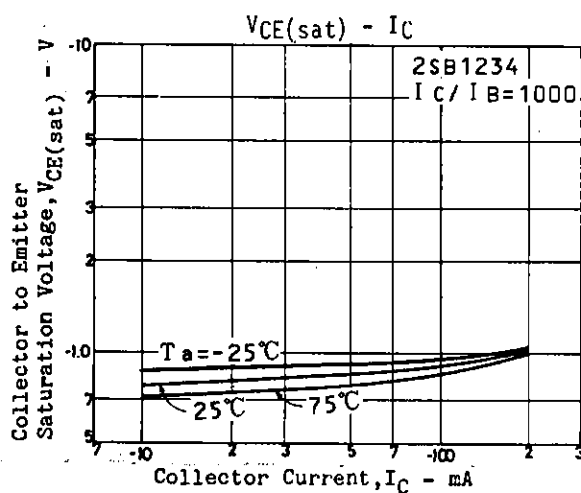
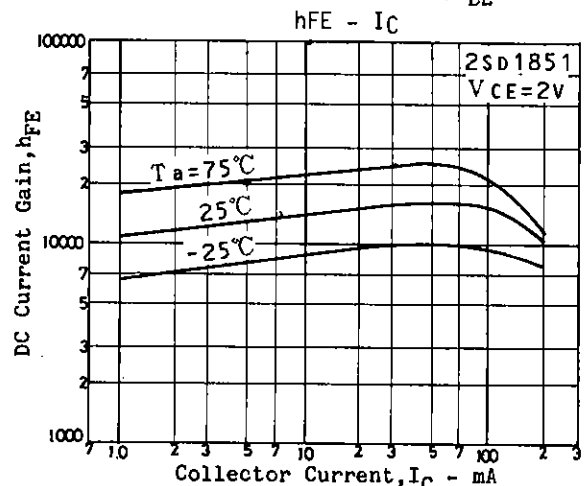
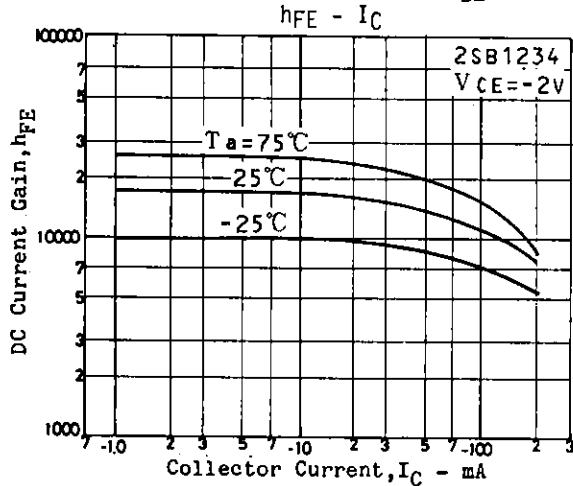
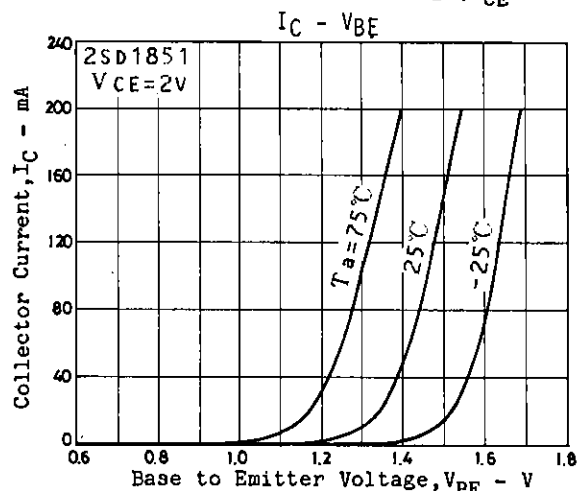
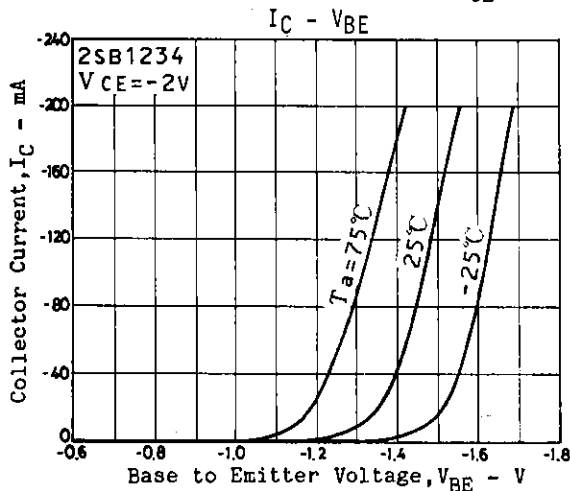
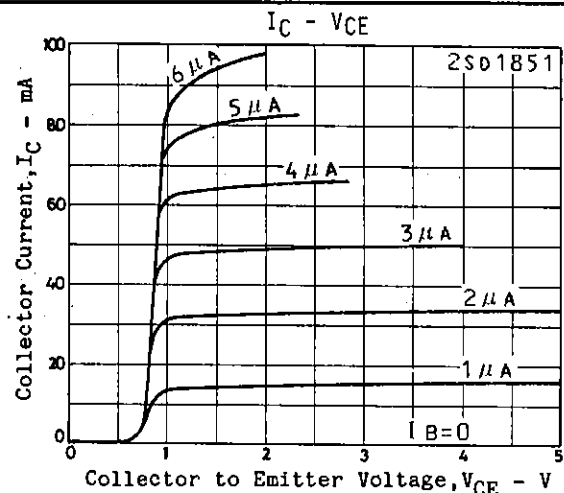
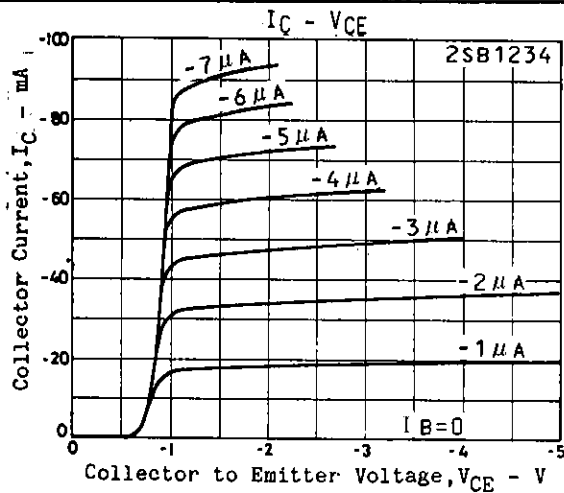


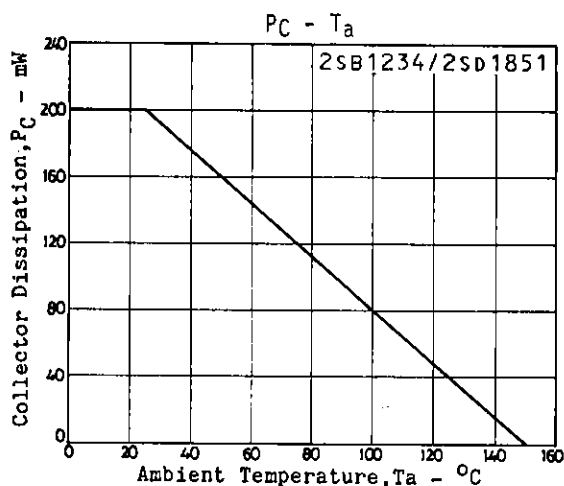
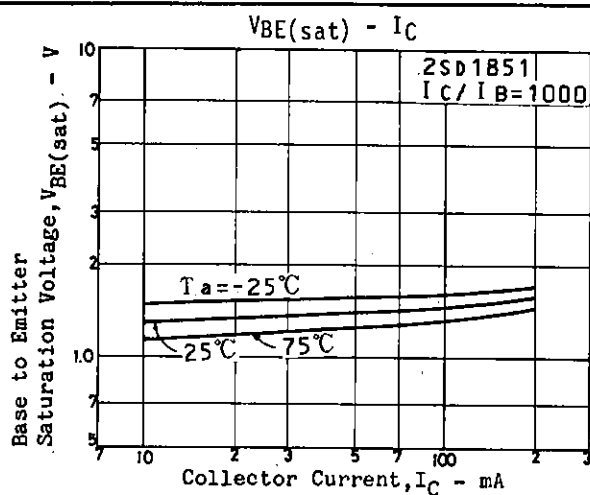
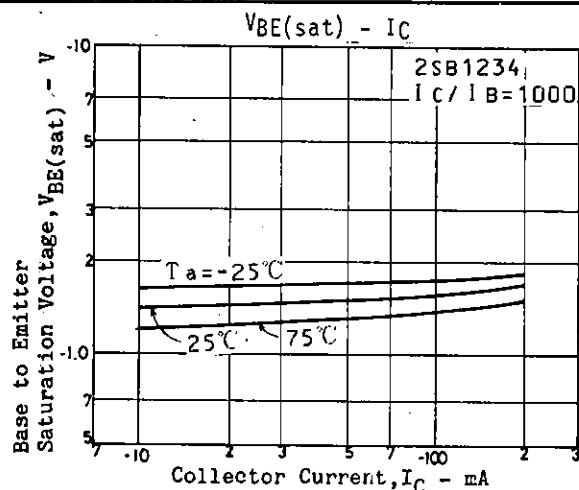
(For NPN, the polarity is reversed.)

Package Dimensions 2018A (unit:mm)



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